

DCR6650H42



Phase Control Thyristor

Preliminary Information

DS6162-1 November 2014 (LN32181)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR6650H42 DCR6650H40 DCR6650H38	4200 4000 3800	$\begin{array}{l} T_{vj} = -40^{\circ}C \ to \ 125^{\circ}C, \\ I_{DRM} = I_{RRM} = 600 mA, \\ V_{DRM}, \ V_{RRM} \ t_p = 10 ms, \\ V_{DSM} \& \ V_{RSM} = \\ V_{DRM} \& \ V_{RRM} \ + 100 V \\ respectively \end{array}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR6650H42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

IS

* Higher dV/dt selections available

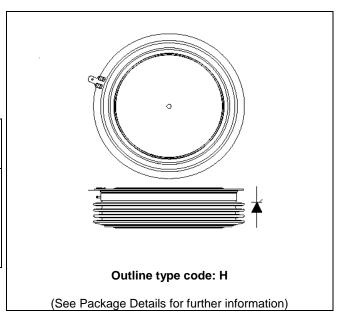


Fig. 1 Package outline





CURRENT RATINGS

 $T_{case} = 60^{\circ}C$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	Double Side Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	6650	А
I _{T(RMS)}	RMS value	-	10446	А
Ι _Τ	Continuous (direct) on-state current	-	9134	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	98.56	kA
l ² t	I ² t for fusing	$V_R = 0$	48.57	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.004255	°C/W
		Single side cooled	Anode DC	-	0.008	°C/W
			Cathode DC	-	0.0093	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 135.0kN	Double side	-	0.0009	°C/W
		(with mounting compound)	Single side	-	0.0018	°C/W
T _{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
Fm	Clamping force			120	155	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	600	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 2x $I_{\text{T(AV)}}$	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω ,	Non-repetitive	-	500	A/µs
		t _r < 0.5µs, T _j = 125°C				
V _{T(TO)}	Threshold voltage – Low level	500 to 4000A at T _{case} = 125°	с	-	0.775	V
	Threshold voltage – High level	4000 to 8000A at $T_{case} = 125$	°C	-	0.977	V
r _T	On-state slope resistance – Low level	500A to 4000A at $T_{case} = 125$	5°C	-	0.124	mΩ
	On-state slope resistance – High level 4000A to 8000A at $T_{case} = 128$		25°C	-	0.076	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω		-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$I_T = 3000A, T_j = 125^{\circ}C,$ $V_R = 200V, dI/dt = 1A/\mu s,$			700	μs
		$dV_{DR}/dt = 20V/\mu s linear$				
Qs	Stored charge	I _T = 3000A, T _i = 125°C, dl/dt – 1A/μs,		2800	6760	μC
I _{RR}	Reverse recovery current	$V_{\text{Rpeak}} \sim 2520 \text{V}, V_{\text{R}} \sim 1680 \text{V}$		42	70	A
ΙL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	A
Ін	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_T = 5A$		-	300	mA





GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM,} T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

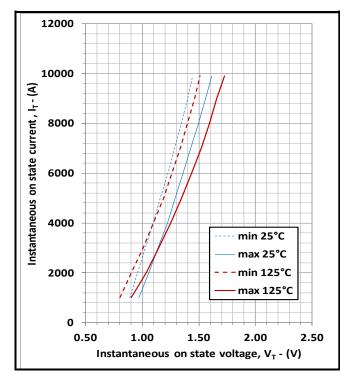


Fig.2 Maximum & minimum on-state characteristics

V_{TM} EQUATION

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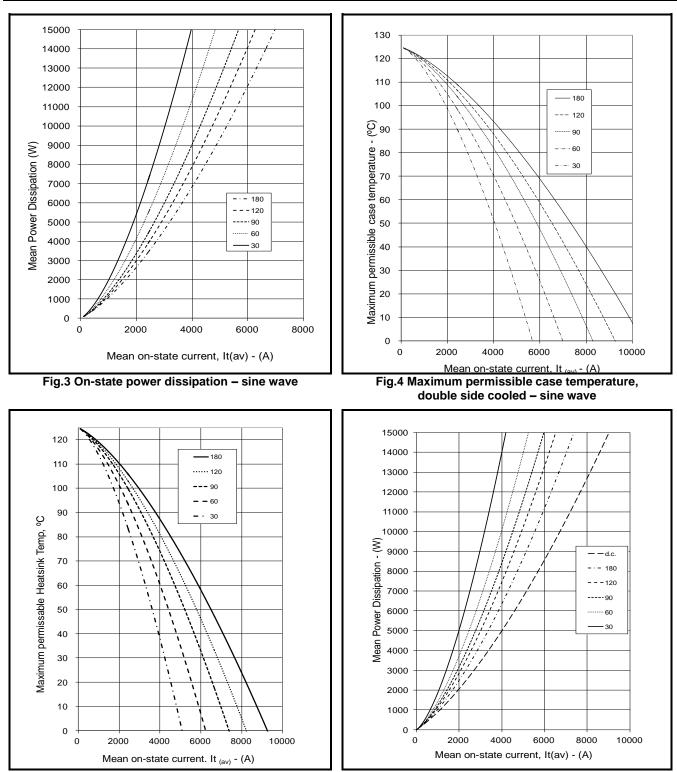
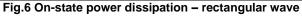
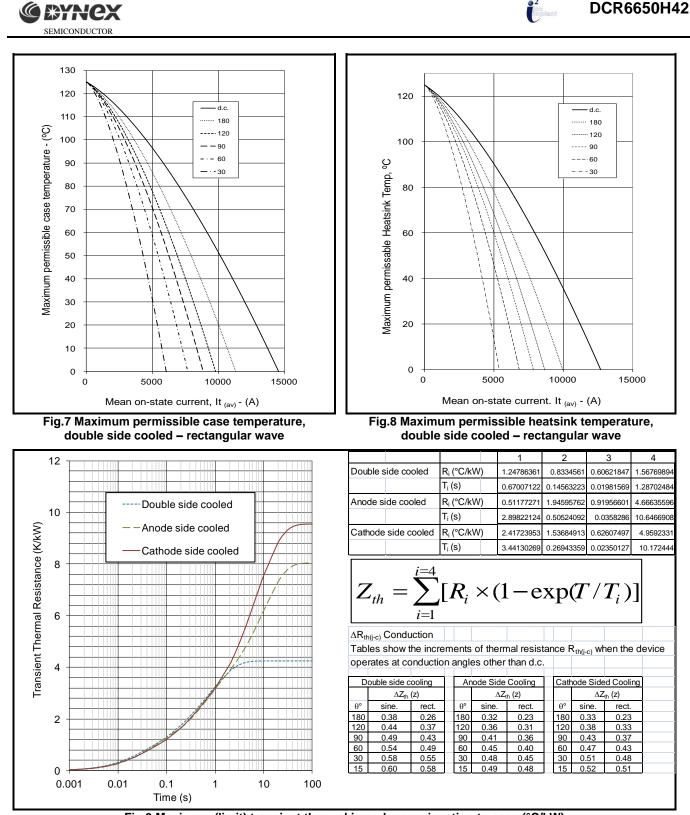
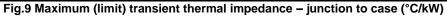
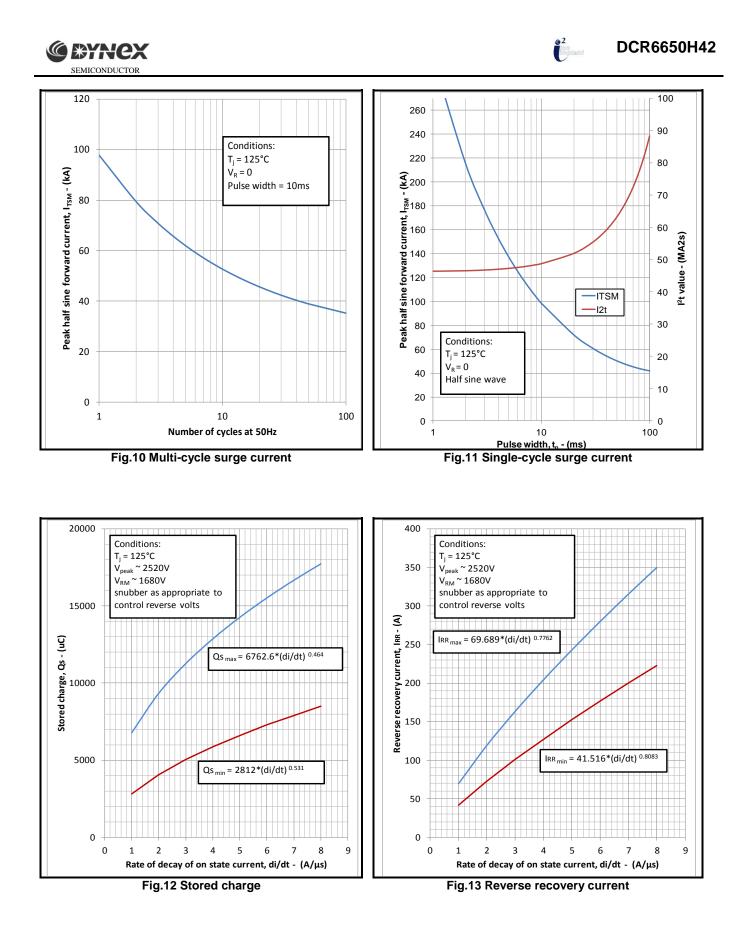


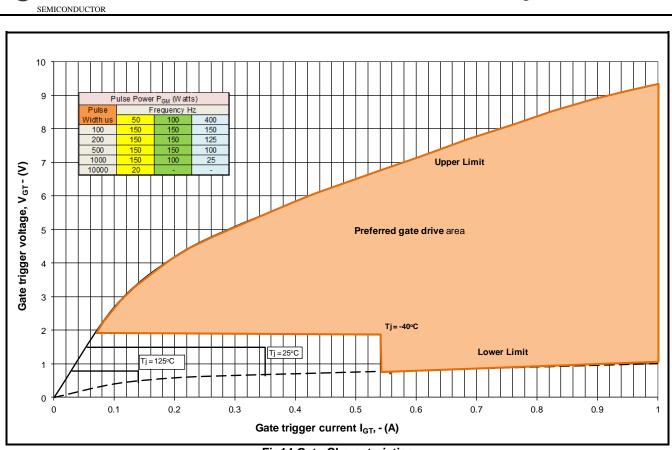
Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave











@2 Insplant DCR6650H42



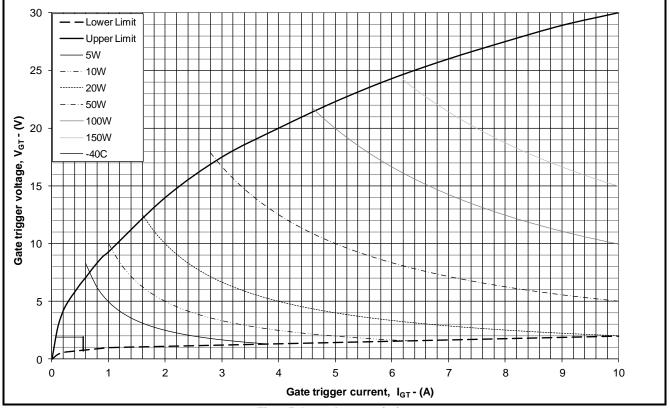


Fig. 15 Gate characteristics

@ BYNEX



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

	Maximum	Minimum	3rd angle projection · \ominus · 🗖 · DD NDT SCALE IF IN DDUBT ASK
Device	(mm)	Thickness (mm)	
DCRXXXH42	35.15	34.28	HOLE Ø3.60 X 4.00 DEEP (IN BOTH ELECTRODES)
DCR6650H42	35.15	34.28	
DCR5240H52	35.27	34.4	
DCR5890H52	35.27	34.4	20° OFFSET (NOMINAL) TO GATE TUBE,
DCR4420H65	35.3	34.7	
DCR4660H65	35.3	34.7	
DCR3640H85	35.65	35.05	
DCR3980H85	35.65	35.05	6.35-+
			Ø170±0.3 Ø115 NOM. GATE Ø115 NOM. Ø115 NOM. Ø115 NOM. Ø115 NOM. Ø115 NOM. Ø115 NOM. Ø1161 MAX.
			Lead length: 420mm Lead terminal connector: M4 ring Package outline type code:H

Fig.16 Package outline





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HEADQUARTERS OPERATIONS

DYNEX SEMICONDUCTOR LIMITED Doddington Road, Lincoln, Lincolnshire, LN6 3LF United Kingdom. Phone: +44 (0) 1522 500500 Fax: +44 (0) 1522 500550 Web: http://www.dynexsemi.com

CUSTOMER SERVICE

Phone: +44 (0) 1522 502753 / 502901 Fax: +44 (0) 1522 500020 e-mail: power_solutions@dynexsemi.com

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